

## High voltage fast-switching NPN power transistor

### Features

- High voltage capability
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed

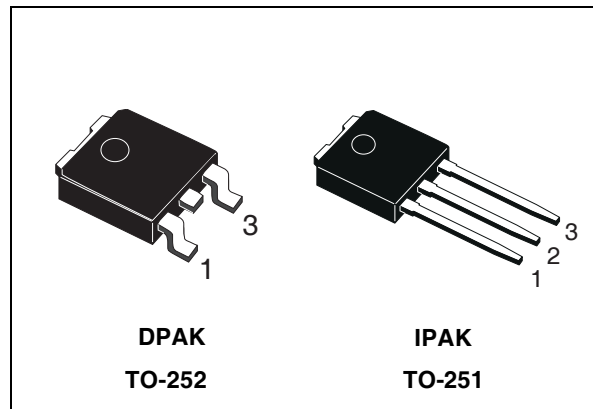
### Description

The device is manufactured using high voltage Multi-Epitaxial Planar technology for high switching speeds and high voltage capability.

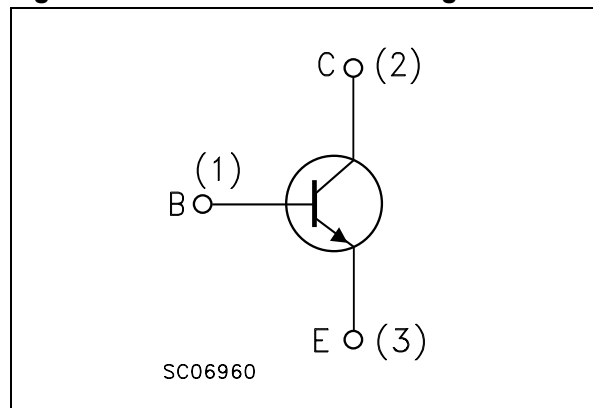
Thanks to an increased intermediate layer, it has an intrinsic ruggedness which enables the transistor to withstand an high collector current level during breakdown condition, without using the transil protection usually necessary in typical converters for lamp ballast.

### Applications

- Electronic ballast for fluorescent lighting
- Switch mode power supplies.



**Figure 1. Internal schematic diagram**



**Table 1. Device summary**

Order codes	Marking	Package	Packaging
BULD741T4	BULD741	DPAK	Tape & reel
BULD741-1	BULD741	IPAK	Tube

# 1 Electrical ratings

**Table 2. Absolute maximum rating**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{BE} = 0$ )	1050	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	400	V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ , $I_B = 2A$ , $t_P < 10ms$ )	$V_{(BR)EBO}$	V
$I_C$	Collector current	2.5	A
$I_{CM}$	Collector peak current ( $t_P < 5ms$ )	5	A
$I_B$	Base current	1.5	A
$I_{BM}$	Base peak current ( $t_P < 5ms$ )	3	A
$P_{tot}$	Total dissipation at $T_C = 25^\circ C$	30	W
$T_{stg}$	Storage temperature	-65 to 150	$^\circ C$
$T_J$	Max. operating junction temperature	150	$^\circ C$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	4.16	$^\circ C/W$

## 2 Electrical characteristics

( $T_{\text{case}} = 25^{\circ}\text{C}$  unless otherwise specified)

**Table 4. Electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{\text{CES}}$	Collector cut-off current ( $V_{\text{BE}} = 0\text{V}$ )	$V_{\text{CE}} = 1050\text{V}$		0.2	10	$\mu\text{A}$
$I_{\text{CEO}}$	Collector cut-off current ( $I_{\text{B}} = 0$ )	$V_{\text{CE}} = 400\text{V}$		10	250	$\mu\text{A}$
$V_{(\text{BR})\text{EBO}}$	Emitter-base breakdown voltage ( $I_{\text{C}} = 0$ )	$I_{\text{E}} = 1\text{mA}$	15	19	24	V
$V_{\text{CEO(sus)}}^{(1)}$	Collector-emitter sustaining voltage ( $I_{\text{B}} = 0$ )	$I_{\text{C}} = 10\text{mA}$	400	450		V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 0.7\text{A}$ $I_{\text{B}} = 0.14\text{A}$ $I_{\text{C}} = 2\text{A}$ $I_{\text{B}} = 0.6\text{A}$		0.15 0.5	0.5 1.5	V V
$V_{\text{BE(sat)}}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = 2\text{A}$ $I_{\text{B}} = 0.6\text{A}$		1.1	1.5	V
$h_{\text{FE}}$	DC current gain	$I_{\text{C}} = 0.1\text{A}$ $V_{\text{CE}} = 5\text{V}$ $I_{\text{C}} = 0.45\text{A}$ $V_{\text{CE}} = 3\text{V}$	48 25	70 35	100 50	
$t_{\text{s}}$ $t_{\text{f}}$	Resistive load Storage time Fall time	$V_{\text{CC}} = 125\text{V}$ $I_{\text{C}} = 1\text{A}$ $I_{\text{B1}} = -I_{\text{B2}} = 0.2\text{A}$ $t_{\text{p}} = 300\mu\text{s}$ $V_{\text{BE(off)}} = -5\text{V}$		2.5 350	3.5 500	$\mu\text{s}$ ns
$E_{\text{ar}}$	Repetitive avalanche energy	$L = 2\text{mH}$ $C = 1.8\text{nF}$ $V_{\text{BE(off)}} = -5\text{V}$	5			mJ

Note (1) Pulsed duration =  $300\mu\text{s}$ , duty cycle  $\leq 1.5\%$

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

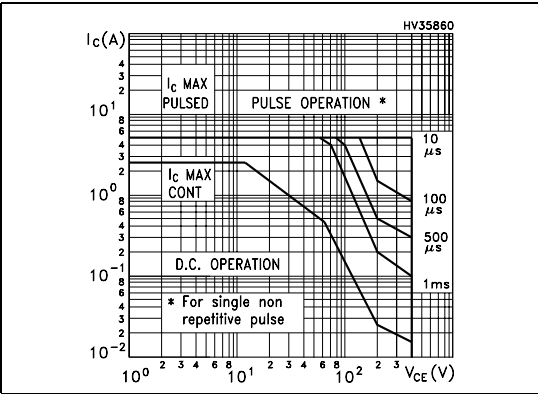


Figure 3. Derating curve

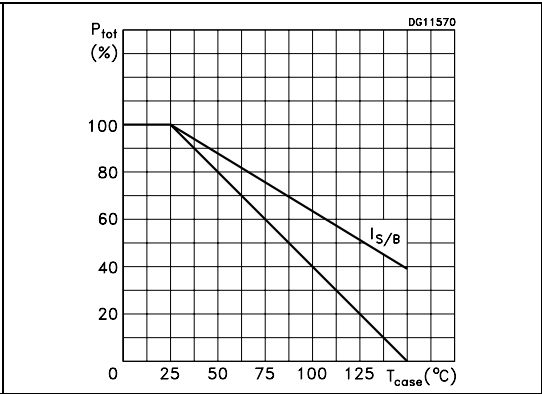


Figure 4. Output characteristics

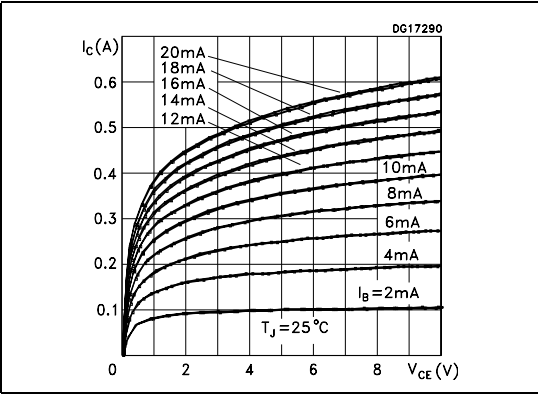


Figure 5. Reverse biased safe operating area

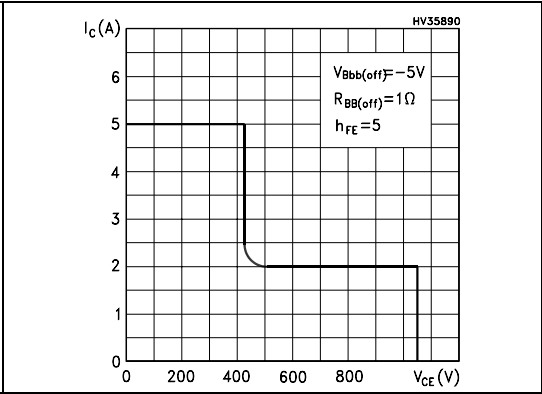


Figure 6. DC current gain

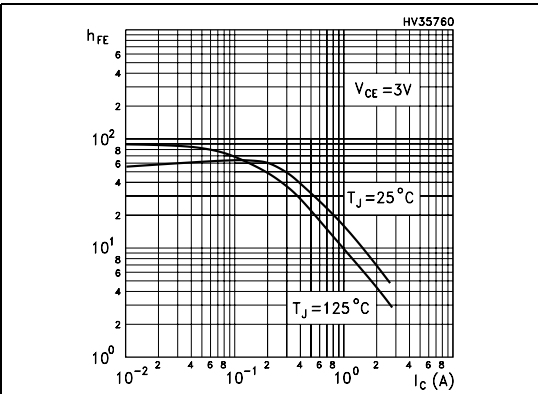


Figure 7. DC current gain

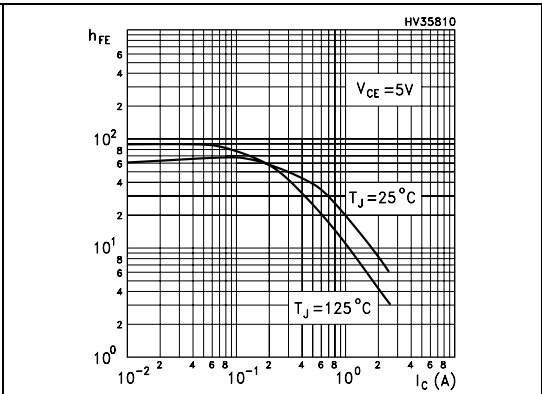


Figure 8. Base-emitter saturation voltage

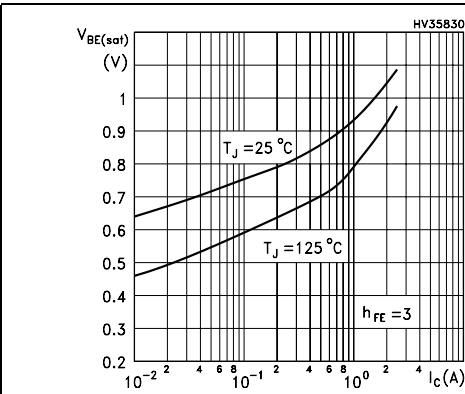


Figure 9. Collector-emitter saturation voltage

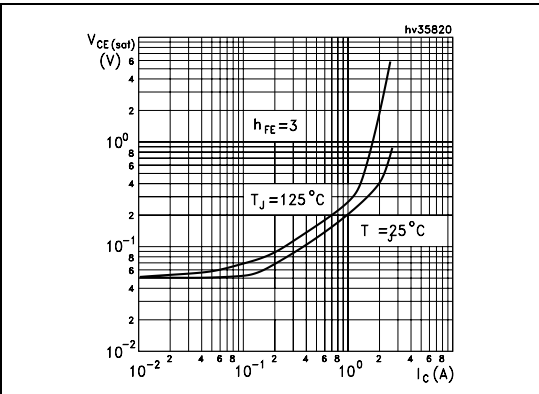


Figure 10. Resistive load switching on times

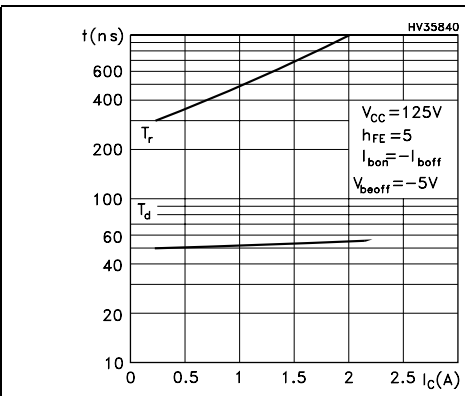


Figure 11. Resistive load switching on times

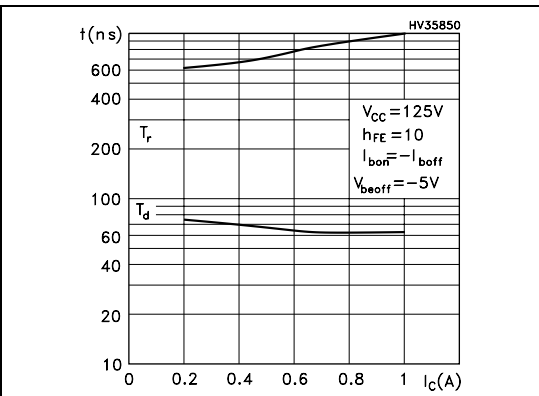


Figure 12. Resistive load switching off times

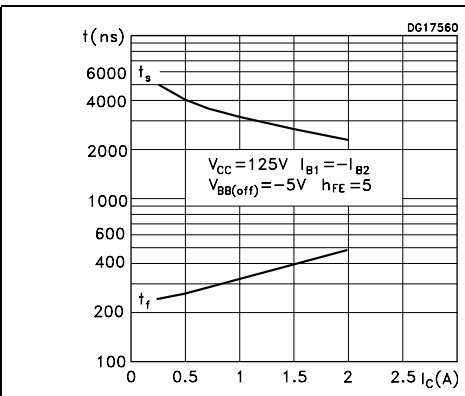
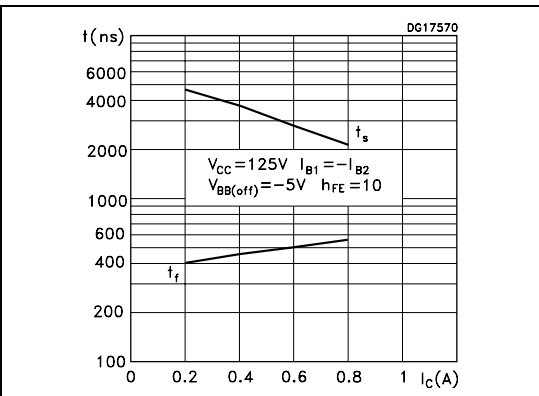
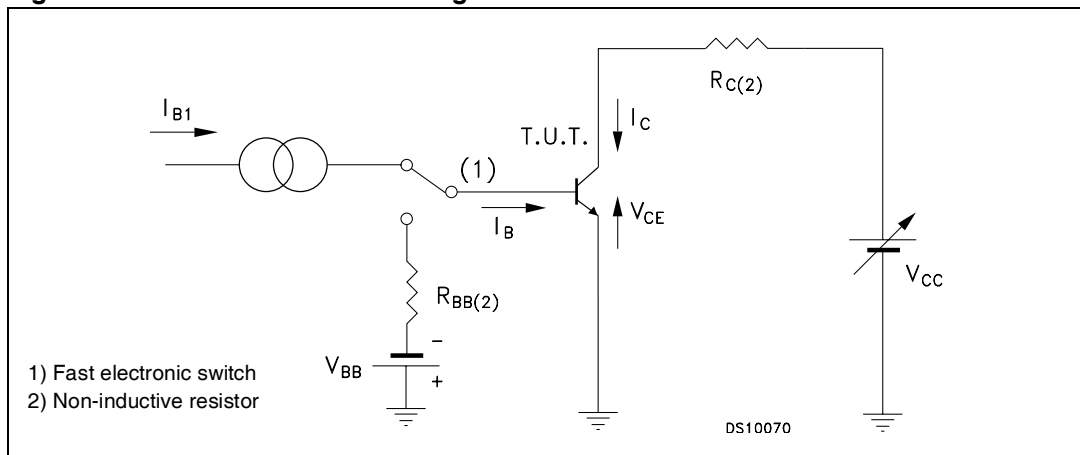


Figure 13. Resistive load switching off times

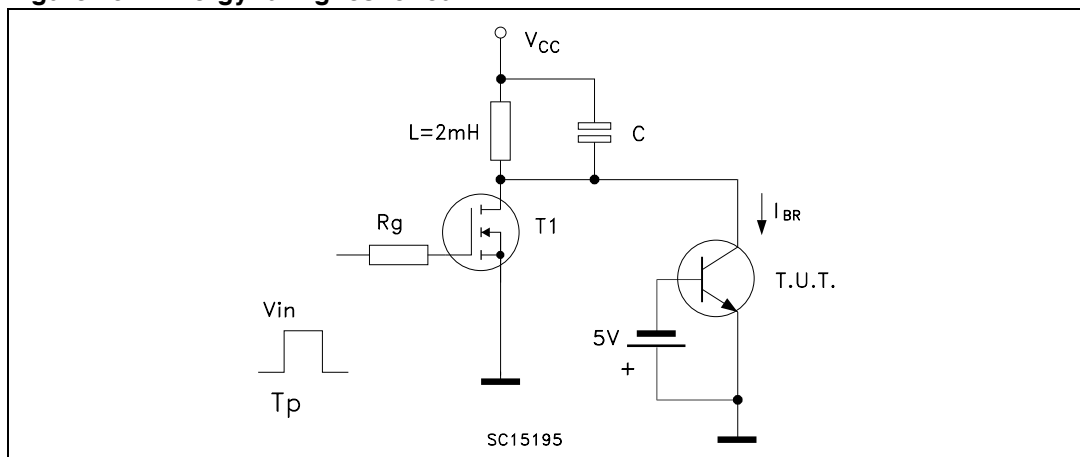


## 2.2 Test circuits

**Figure 14. Resistive load switching test circuit**



**Figure 15. Energy rating test circuit**

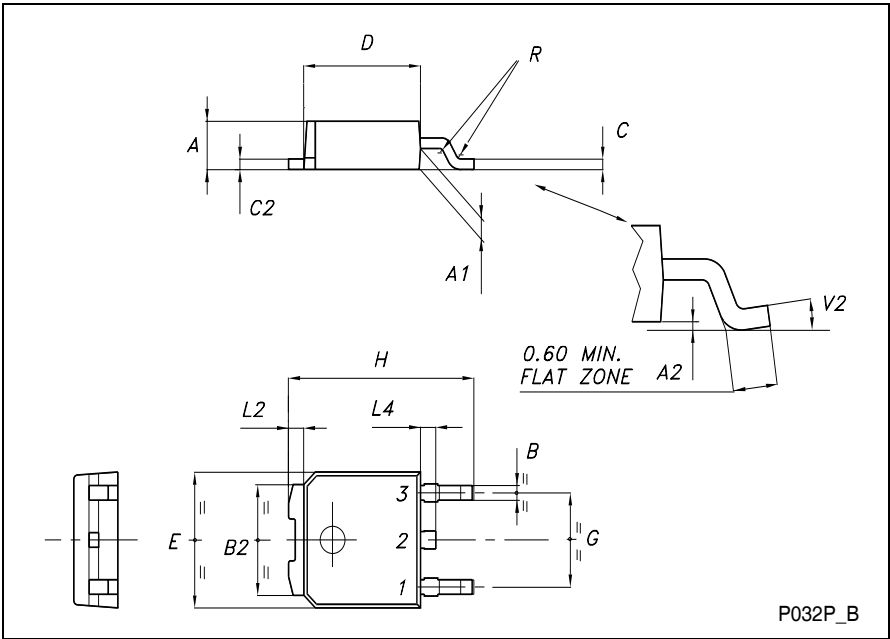


### 3      **Package mechanical data**

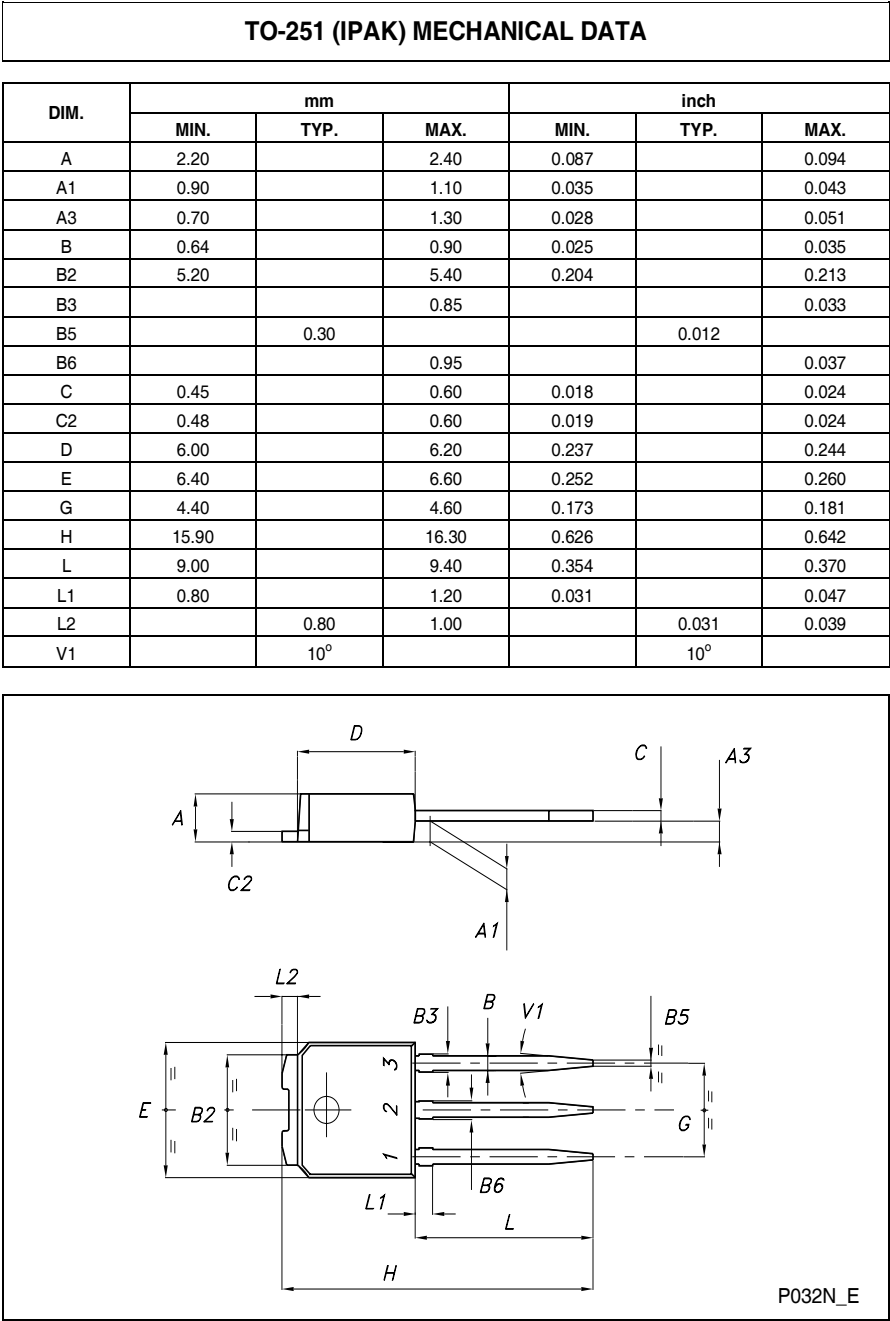
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°







## 4 Revision history

**Table 5. Revision history**

Date	Revision	Changes
20-Dec-2006	1	Initial release.
09-Jul-2007	2	Updated package names in page 1, added figure 4, updated figure 12 and 13.

**Please Read Carefully:**

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

**UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.**

**UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED REPRESENTATIVE OF ST, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS, WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.**

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2007 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

[www.st.com](http://www.st.com)

